#### Curriculum for M.Tech

#### Electronics and Communication Engineering With Specialization in Microelectronics and VLSI Systems

(From The Academic Year 2021)

Approved by Senate-44



Indian Institute of Information Technology, Design and Manufacturing, Kancheepuram

Chennai-600 127

	PROPOSED	M.TECH CURRICULUM 2021 (Microe	electronics and	VLSI	Syst	ems)	
		Semester 1					
S.No	Couse Code	Course Name	Category	L	T	P	$\mathbf{C}$
1	EC5009	MOSFET Modelling for VLSI Circuits	PCC	3	1	0	4
2	EC5010	Analog IC Design	PCC	3	1	0	4
3	EC5011	VLSI Testing and Testable Design	PCC	3	1	0	4
4		Elective Course 1	ELC	3	1	0	4
5		Elective Course 2	ELC	3	1	0	4
6	EC5012	Device Modelling and Simulation Practice	PCC	0	0	3	1.5
7	EC5013	SoPC and VLSI Testing Practice	PCC	0	0	3	1.5
			•				23.0
Ц		Semester 2					
S.No	Course Code	Course Name	Category	L	T	P	С
1	EC5014	Digital IC Design	PCC	3	1	0	4
2	EC5015	VLSI System Design	PCC	3	1	0	4
3	EC5016	VLSI Technology	PCC	3	1	0	4
4		Elective Course 3	ELC	3	1	0	4
5		Elective Course 4	ELC	3	1	0	4
6	EC5017	IC Design Practice	PCC	0	0	3	1.5
7	EC5018	Verification Practice	PCC	0	0	3	1.5
	_		•				23.0
		Semester 3					
S.No	Course Code	Course Name	Category	L	Т	P	С
1	EC6000	Project I (Summer Project)	PCD	0	0	20	10
2	EC6001	Project II	PCD	0	0	32	16
							26.0
		Semester 4		•			
S.No	Course Code	Course Name	Category	L	Т	P	C
1	EC6002	Project III	PCD	0	0	32	16
							16.0

#### Semester wise Credit Distribution

Category	Semester wise Credit						
	S1	S2	Summer	S3	S4	Total	%
Professional Core Course (PCC)	15	15	0	0	0	30	34.1
Elective Course (ELC)	8	8	0	0	0	16	18.2
Professional Career Development (PCD)	0	0	10	16	16	42	47.7
Total	23.0	23.0	10.0	16.0	16.0	88.0	100.0
	23.0	46.0	56.0	72.0	88.0		

Course Name	MOSFET Modelling for VLSI Circuits	Course Code	EC5009				
Offered by Department	Electronics and Communication Engineering	Structure( LTPC)	3	1	0	4	
To be offered for	M.Tech	Course Type	Core		l	I	
Prerequisite	Basics of Semiconductor Devices, Digital Electronics	Approved In	Senate-4	14			
Learning Objectives	devices  To describe and use physics-kinclusion in circuit application	pased numerical an	semiconductor physics relevant to d analytical device modelling for the				
Learning Outcomes	Relate the models for further	Model any kind of MOS Devices in 2-D or 3-D Relate the models for further inclusion in circuits					
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	Transconductance, Source-D and Equivalent Circuits, C Model, RF Models (11L+2T)	General Analysis, actitance, Three-Te tor, Introduction Andels, Source Reference Locity Saturation, Carier Lowering, Hot on Depletion (6L+2 delling for Circuits anction Leakage, of Good Models, Beact Models, Benchi Conductance Parameters Due train and Output Cotapacitance Evaluation	Inversion rminal MC all-Region rence vs. I Channel Le Carrier E L) s Simulati Scaling Model Formark Tests meter Defeation and	, Strong OS Stru Models Body R ength M ffects, ' fon- Qu and N rmulation s (7L+3 finition and e, Capa	g Invers cture (71 cture (	ion, Weak L+3T) Inversion Effective on, Charge Overshoot Mechanical chnologies, derations, Equivalent Leakage, Definitions Parameter	
Essential Reading	1. Y. Tsividis and C. McAndrew, MC University Press, 2011			Simula	tion, Oxf	ford	
Supplementary Reading	<ol> <li>BSIM Manuals available on BSIM</li> <li>T. A. Fjeldly, T. Yetterdal and M. Simulation, John Wiley, 1998.</li> <li>Y. Taur and T. H. Ning, Fundame Press, 1998.</li> <li>Y. P. Tsividis, Mixed Analog-digit Publishing Co Pte Ltd, 2002</li> </ol>	I. Shur, Introducti	ion to Dev 'LSI Devic	es, Can	nbridge 1	University	



Course Name	Analog IC Design	Course Code	EC5010				
Offered by	Electronics and Communication	Structure	2	1	0	4	
Department	Engineering	(LTPC)	3	1	0	4	
To be offered for	M.Tech	Course Type	Core				
Prerequisite	NIL	Approved In	Senate	-44			
Learning Objectives	<ul> <li>To impart in depth knowledge design and analysis of operati</li> <li>To be capable of designing an</li> </ul>	onal amplifiers an	d circuits	circuits using them ecifications			
Learning Outcomes	<ul> <li>To analyses effect of mismatch between components in the performance of ICs</li> <li>To model MOSFET in IC</li> <li>To analyses noise in different components in the IC</li> <li>To derive the Data Sheet / Specifications of Single stage, two stage, folded casca opamps</li> <li>To understand fully differential operation, opamp and make such circuits</li> </ul>						
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	<ul> <li>(4L+2T)</li> <li>MOS Transistor: Layout, mode</li> <li>Noise: Noise in Resistor, capade</li> <li>Single stage opamp: Noise, of Analysis in two and higher of Cascode current mirror, Compensated op amps. (8L+2</li> <li>Fully differential circuits and PLL (6L+2T)</li> <li>Tutorials will include pen-padayout level</li> </ul>	<ul> <li>Components and mismatch in CMOS process, models and Layout techniques (4L+2T)</li> <li>MOS Transistor: Layout, model, Body effect, transit frequency. (4L+2T)</li> <li>Noise: Noise in Resistor, capacitor, and MOSFET, spectral density (4L+2T)</li> <li>Single stage opamp: Noise, offset, swing limits and slew rate, Loop gain and stabilit Analysis in two and higher order opamp (10L+2T)</li> <li>Cascode current mirror, Cascode, Folded Cascode multi stage and Mille compensated op amps. (8L+2T)</li> <li>Fully differential circuits and opamp, common mode feedback circuits. (6L+2T)</li> <li>PLL (6L+2T)</li> </ul>					
Essential Reading	1. Behzad Razavi, Design of Analog Education, 2016, ISBN: 978-0-07-	252493-2					
Supplementary Reading	<ol> <li>Tony Chan Carusone, David A. Jo Design, John Wiley &amp; Sons, Inc.,</li> <li>Paul R. Gray, Paul J. Hurst, Step Of Analog Integrated Circuits, 5t. 470-24599-6.</li> <li>Tertulien Ndjountche, CMOS Ana Efficient Design, CRC Press Taylor</li> </ol>	2012, ISBN: 978-0- hen H. Lewis, Rob- h edition, John Wil alog Integrated Cir	-470-7703 ert G. Me ley & Son cuits Hig	10-8. eyer, Ana is, Inc., 2 gh-Speed	alysis and 2009. ISE	d Design BN: 978-0-	

Course Name	VLSI Testing and Testable Design	Course Code	EC50	11					
Offered by	Electronics and Communication	Structure(LTP	3	1	0	4			
Department	Engineering	C)	Э	1	U	4			
To be offered for	M.Tech	Course Type	Core						
Prerequisite	Basics of Digital Electronics	Approved In	Senat						
Learning Objectives	The course aims at imparting	=	_	gn of an e	fficient t	estable			
Dearning Objectives	circuit and optimal test vecto								
	• At the end of the course, the								
Learning Outcomes	<ul> <li>Model the faults in the combination and sequential circuits</li> </ul>								
Learning Outcomes	Perform the fault analysis and test pattern generation using ATPG algorithms								
	Build the testable circuit wit	h test vectors.							
	Basic of Test and Role of HDI	L - Design and Test,	Test Co	ncerns, l	HDLs in	Digital			
	System Test, ATE Architectu	re and Instrumentat	tion.	(3L+1'	Γ)				
	Verilog HDL for Design and T	Test: Using Verilog in	n Design	n, Using	Verilog i	in Test,			
	Basic Structures of Verilo	g, Combinational	Circuits	s, Seque	ential C	ircuits,			
	Testbench Techniques. (3L+1	T)							
	• Fault and Defect Modelling: Fault Modelling, Structural Gate Level Faults,								
	Issues Related to Gate Level Faults, Fault Collapsing in Verilog. (5L+2T)								
	Fault Simulation Application and Methods: Fault Simulation, Fault Simulation								
	Applications, Fault Simulation Technologies. (5L+1T)								
	• Test pattern Generation Methods and Algorithm: Test Generation Basics,								
	Controllability and Observability, Random Test Generation. (4L+1T)								
Course Contents (with	Deterministic Test Generation Algorithms: Deterministic Test Generation								
approximate breakup of hours for lecture/	Methods, Sequential Circuit Test Generation, Test Data Compaction. (4L+1T)								
tutorial/practice)	Design for Test by Means of Scan: Making circuits Testable, Testability Insertion,								
tatorian practice)	Full Scan DFT Technique, Scan Architectures and RT level Scan Design. (4L+2T)								
	Standard IEEE Test Access	Methods: Boundary	y Scan	Basics,	Boundar	y Scan			
	Architecture, Boundary Sca	an Test Instruction	ns, Boa	rd Leve	el Scan	Chain			
	Structure, RT level Boundary Scan and Boundary Scan Description Language.								
	(5L+2T)								
	Logic Built-in Self-test: BIST	Basics, Test Pattern	n Gener	ation, O	utput Re	esponse			
	Analysis, BIST Architectures	, RT Level BIST Des	sign. (4	L+1T)					
	Test Compression: Test Data Compression, Compression Methods and								
	Decompression Methods. (3L	+1T)							
	Memory Testing by Means of	Memory BIST: Mem	ory Tes	ting, Me	mory Str	ucture.			
	(2L+1T)								
Essential Reading	1. Zainalabedin Navabi, Test					ls and			
Essential Reading	Architecture, 1st edition, Spr								
		1. M. Abramovici, M. A. Breuer and A. D. Figriieta, Digital Systems Testing and							
	Testable Design, Wiley-IEEF 2. Niraj K. Jha, Sandeep Gupta					hridae			
Supplementary	University Press, 2003. ISBN		ystems	, isi eun	non, Can	ibriage			
Reading			entials o	of Electro	onic Test	ting for			
		3. Michael L. Bushnell, Vishwani D. Agrawal, Essentials of Electronic Testing for Digital, Memory, and Mixed-Signal VLSI Circuits, Springer, 2004. ISBN: 7923-							
	7991-8.	=							

Course Name	Device Modelling and Simulation Practice	Course Code	EC5012	2			
Offered by Department	Electronics and Communication Engineering	Structure(LTP C)	0	0	3	1.5	
To be offered for	M.Tech	Course Type	Core				
Prerequisite	NIL	Approved In	Senate				
Learning Objectives	<ul> <li>To make the students familian</li> <li>To impart a flavour of differ simulation tools.</li> <li>The lab is intended to teach s to design the device structure device modelling tools.</li> </ul>	ent semiconductor	device i	modelling	g with the provide	confidence	
Learning Outcomes	At the end of the course, students won  simulate and analyse structures dimensional device structures	eture, doping pro ent, field, potential	and ener	gy band	diagram	s within 2-	
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	of device and process simulati  Device simulation: observing carriers, current, field, potent  Process simulation: observation  Simulation of 2-D MOSFETs to Simulation of novel 3-D transdevices, solar cells etc, through	of device and process simulations.  • Device simulation: observing the terminal characteristics and distributions of carriers, current, field, potential and energy band diagrams within the device.  • Process simulation: observation of device structure and doping profile  • Simulation of 2-D MOSFETs through device and process simulations  • Simulation of novel 3-D transistors such as III-V HEMT, LEDs, FinFETs, GAA devices, solar cells etc, through device simulation					
Essential Reading	<ol> <li>C K Maiti, "Introducing Technol Simulations, and Applications", Je 9814745512.</li> <li>Wu, Yung-Chun, Jhan, Yi-Ruei, "3 Springer, 2017, ISBN 978-981-10-</li> </ol>	enny Stanford Publ ED TCAD Simulatio 3066-6.	ishing; 1 <sup>s</sup> on for CM	st Edition	n, 2017, I peletroni	SBN: 978- c Devices",	
Supplementary Reading	<ol> <li>C K Sarkar, "Technology Compute Press, 1st Edition, 2013, ISBN: 978</li> <li>JP. Colinge, "FinFETs and Othe 0-387-71751-7</li> <li>TCAD Manual (Available Online)</li> </ol>	8-1466512658.					

Course Name	SoPC and VLSI Testing Practice	Course Code	EC5013	3		
Offered by	Electronics and Communication	Structure(LTP	0	0	0	1 5
Department	Engineering	C)	0	0	3	1.5
To be offered for	M. Tech	Course Type	Core			
Prerequisite	NIL	Approved In	Senate			
Learning Objectives	Design and development complete har	rdware/software sy	stem on I	FPGA an	d VLSI t	esting
Learning Outcomes	Student can able to design and develop the hardware/software system on FPGA, can a to effectively use commercially available building block (IP) to construct highly integral systems, can able to efficiently break down complex computational tasks into hardward software components and build co-processor.  • Verify fault coverage of test patterns, simulate fault, apply test pattern, a					grated
Course Contents (with approximate breakup of hours for lecture/tutorial/practice)	observe output  Hands-on on Design for test testability  Writing ATPG and Designs for Implement BIST for Memory  Scan Chain based Sequential  Fault Models simulations and  Implement path delay fault t  Introduction to System-On-Cland Recoding  Protocol and Interface, System  Electronic system level model Design, Network on chip and  SoC Engineering and associatevel Design Capture and Sy	(DFT) – insert tes or Combinational a blocks Circuit Testing I verifications, Stru- esting hip, Register Trans m-C Components, I lling, Transactional Bus Structures ated Tools, Archite	t points, nd Seque ctural Te fer Langu Basic SoC I level mo	scan cha ential Cir esting with uage, Fol Compondelling, A	ins, to incuits.  th Fault I ding, Re- ents, Assertion	Models timing a based
Essential Reading	<ol> <li>Wang, "VLSI Test Prir Elsevier; First edition (1</li> <li>Louise H. Crockett, Stewart, The Zynq Book the Xilinx Zynq-7000 A ISBN: 099297870X.</li> </ol>	January 2011). IS Ross A. Elliot, M : Embedded Proces	BN: 9380 lartin A. sing with	501552 Enderw the ARI	ritz, Rob M Cortex	ert W.
Supplementary Reading	<ol> <li>Wayne Wolf, FPGA base ISBN: 0131424610.</li> <li>Steve Furber, ARM S Wesley, 2000. ISBN: 020</li> </ol>	System on Chip Are				

Course Name	Digital IC Design	Course Code	EC501	4					
Offered by	Electronics and Communication	Structure(LTP	3	1	0	4			
Department	Engineering	C)			Ů	1			
To be offered for	M Tech	Course Type	Core						
Prerequisite	NIL	Approved In	Senate						
Learning Objectives	design procedures for comple subsystems.								
Learning Outcomes	using tool for higher level  To model MOSFETs and Into To determine Noise margins, ICs To develop combinational an and Pass Transistors To build arithmetic and Men	Interconnects in ICs gins, switching voltage, delay parameters, power etc. in I and sequential circuits with static and dynamic CMOS							
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	<ul> <li>Issues in Digital Integrated 0</li> <li>Fabrication of CMOS IC and</li> <li>MOS Device: Threshold Volt</li> <li>Interconnect: Parameters, El</li> <li>CMOS Inverter: Transfer Ch</li> <li>Propagation Delay, Power (5</li> <li>Combinational Logic Circuits</li> <li>Dynamic Logic, Cascading (7</li> <li>Sequential Logic Circuits: Ti</li> <li>C2MOS, NORA-CMOS (7L+2)</li> <li>Arithmetic Building Blocks:</li> <li>Memory and Array Structure</li> <li>Flash Memory (5L+2T)</li> <li>Tutorials will include pen-palayout level</li> </ul>	packaging (4L+1T) age, Secondary Effe lectrical Wire Mode aracteristics, Noise L+2T) s: Static CMOS, Pa (L+2T) ming Metrics, Stat (2T) Data paths in Digit es: ROM, RAM, CA	ects, SPIC els, SPIC e margin, ss-Trans ic and Dy al Proces M, Perip	E Wire M. Capacit istors, D. vnamic L. ssor Arch heral Cir	Models (2 cances, ynamic ( catches, I nitecture reuitry, I	L+1T) CMOS, Registers, s (7L+2T) PLA and			
Essential Reading	1. Jan M. Rabaey, Anantha Ch Circuits, 2 ND edition, Pears 0130909961	son, 2003. ISBN-10	: 0130909	9963, ISI	3N-13: 9′	78-			
Supplementary Reading	1. John E. Ayers, Digital Integr Press, 2009. ISBN-10: 14200 2. R. Jacob Baker, CMOS Circu Blackwell, 2010. ISBN-10: 04 3. Sung-Mo (Steve) Kang, Yusu Circuits Analysis & Design, 4 ISBN-10: 0073380628. ISBN	6987X, ISBN-13: 9 uit Design, Layout, 470881321, ISBN-1 of Leblebici, Chilwo 4th edition, McGra	78-14200 and Simu 3: 978-04 o Kim, C w-Hill Hi	69877. ulation, 3 17088132 MOS Dig	3rd editio 23. gital Inte	on, Wiley-			

Course Name	VLSI System Design	Course Code	EC5018	5		
Offered by Department	Electronics and Communication Engineering	Structure(LTP C)	3	1	0	4
To be offered for	M.Tech	Course Type	Core	I		
Prerequisite	NIL	Approved In	Senate	-44		
Learning Objectives	To impart in depth knowledge in the d including both digital and analog buil	-	nd analys	ses of con	nplex VL	SI circuits
Learning Outcomes	At the end of the course, students wo  Understand circuits and sy integrated circuits  Design and analyze comple verification tools Gain proficiency in hardware	vstem level issues ex VLSI systems	using in	ndustry		
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	<ul> <li>Review of VLSI, Classification implementation options of VLS Modeling Styles (L5+1T)</li> <li>Designing Fast CMOS Circuit Effort and Optimization, Low Techniques at Circuit and Sy mitigation Techniques. (L8+T</li> <li>VLSI system design with HD dataflow, structural and mixed designs. Data path subsystem arithmetic circuits and interest and design verification included interconnect Design: Design Parasitic, Interconnect Techn Distribution Networks, Clock Designs: Design consideration reliability. (L7+T2)</li> <li>Input/output Modules and ESD Drivers, and ESD Protection (L5+T2)</li> </ul>	Is Systems. Y-Charts, Various Technic Power Design Techstem Levels, Trade (3)  L: Module concepts ed style modeling, Son design: Combinationnects; implementing post layout similar issues with Resistivatiques, Power Districtions for signal integrities. OP Protection Network Circuits, Overall Systems	t, Design ques for E nniques, I offs in Po and mod Synthesis ional and tation of a nulations. ve, Capac ibution an istributio ity, manu rorks: Inp	Abstract Delay Est Power M wer & D leling sty and ver sequent such sys (L7+T2) itive and nd Clock n Acturab ut Buffe sign exa	tion Leve timation, anageme delay and vles: Beha ification of tial circuitems with tems with Design: rks, Layo collity and rs, Outpu	ls. Logical nt avioral, of ts, n HDL re Power out
Essential Reading	Ming-Bo Lin, Introduction to VLSI Stress, 2012, ISBN: 978-1-4398-6859.	ystems A logic, circ	uit and S	ystems I	Perspectiv	ve, CRC
Supplementary Reading	<ol> <li>Neil H. E. Weste, David Money Perspective, 4<sup>th</sup> edition, Addison-</li> <li>Liming Xiu, VLSI Circuit Design IEEE Press, A John Wiley &amp; Son</li> <li>Hubert Kaeslin, Morgan Kaufm ISBN: 978-0-12-800730-3.</li> </ol>	Wesley, Pearson, 2 n, Methodology Den is, Inc., 2008, ISBN	013, ISB mystified : 978-0-4	N: 978-0 , A conce 70-12742	-321-5477 eptual Ta 2-1.	74-3. exonomy,

Course Name	VLSI Technology	Course Code	EC501	6			
Offered by Department	Electronics and Communication Engineering	Structure(LTP C)	3	1	0	4	
To be offered for	M.Tech	Course Type	Core	•	•		
Prerequisite	NIL	Approved In	Senate	-44			
Learning Objectives	<ul> <li>To bring both Circuits and System views on technology together.</li> <li>To offer a profound understanding of the design of complex VLSI devices, and synthesis tools for fabrication.</li> </ul>						
Learning Outcomes	At the end of the course, students wor      Appreciate the intricacies involved      Understand the various proce     Learn fabrication steps for ex	olved in VLSI circu sses needed to fabr isting and coming g	abricate the VLSI devices. ng generation devices.				
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	<ul> <li>Introduction to VLSI Design, Fabrication. (L4+T1)</li> <li>Crystal Structure of Si, Defecting (L4+T1)</li> <li>Oxidation – Kinetics, Rate (L5+T2)</li> <li>Diffusion-Theory of Diffus Implantation - Process, Ann (L5+T2)</li> <li>Lithography, immersion lithotether materials (L3+T1)</li> <li>Deposition-Plasma Deposition contacts, Copper interconnecting IC BJT - LOCOS, Trench isolated for high-speed applications (L</li> <li>MOSFET - Metal gate vs. Selecthon CMOS Technology, Latch - channels and high-k gate diel</li> </ul>	ts in Crystal, Crystay, Doping during Is constants, Dopant ion, Doping Propealing of Damages graphy, e-beam litting, Dry Etching, Plan, Metallization, s (L4+T1) ation, Poly-emitter-3+T1) f-aligned Poly-gate, up in CMOS, MO	cal growt Epitaxy, I Redistri- files, D s, Maskin nography asma Etc Problems poly-base Tailorin	h (L3+T: Molecula ibution, biffusion ng durin (L5+T2) ching, Si s in Alu e-BJT ar	Oxide C System g Implan , SiO <sub>2</sub> , S uminium ad its suit ice Parar s with st	Epitaxy harges s Ion ntation iN and Metal cability meters,	
Essential Reading	S. K. Ghandhi, VLSI Fabrication Princ						
Supplementary Reading	1. S. M. Sze, VLSI Technology, 7 2. J. Plummer, M. D. Deal, P. Fractice and Modeling, Pears	Tata McGraw Hill, 3. Griffin, Silicon V	2008 'LSI Tecl			entals,	

Course Name	IC Design Practice	Course Code	EC501	7			
Offered by	Electronics and Communication	Structure(LTP	0	0	0	1 5	
Department	Engineering	C)	0	U	3	1.5	
To be offered for	M Tech	Course Type	Core				
Prerequisite	NIL	Approved In	Senate	-44			
Learning Objectives	<ul> <li>To impart in depth knowledge analog integrated circuits es amplifiers and Digital integra</li> <li>Students would be able to des circuits using industry level a</li> </ul>	specially operation ted circuits. ign and analyse co	al ampli mplex ar	fiers an	d trans	conductor	
Learning Outcomes	<ul> <li>To be capable of simulating Schematic level analog circuits with at least 20 transistors</li> <li>To be capable of generating layout with full custom / semicustom tools and to perfore post layout simulations and extracting parameters to schematic model</li> <li>To design Digital building blocks using VHDL / Verilog</li> <li>To generate synthesizable design, create layout and post layout simulations for ASIO Design</li> </ul>						
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	Synopsys tools (6 weeks)  • Design of digital building blo Cadence and Synopsys tools • Project will include identify IEEETCASI, IEEE TCASII,	<ul> <li>Design of analog ICs with Schematic and layout simulation using Cadence and Synopsys tools (6 weeks)</li> <li>Design of digital building blocks with Schematic and layout simulation using Cadence and Synopsys tools (6 weeks)</li> </ul>					
Essential Reading	<ol> <li>Behzad Razavi, Design of An Hill Education, 2016, ISBN: 9</li> <li>Jan M. Rabaey, Anantha Cha Circuits, 2nd edition, Pearson 0130909961.</li> </ol>	978-0-07-252493-2 andrakasan, Borivo , 2003, ISBN-10: 0	oje Nikoli 13090996	ic, Digita 33, ISBN	l Integra -13: 978	ited	
Supplementary Reading	<ol> <li>Tony Chan Carusone, David Circuit Design, John Wiley &amp;</li> <li>Paul R. Gray, Paul J. Hurst, Design Of Analog Integrated ISBN: 978-0- 470-24599-6</li> <li>Sung-Mo (Steve) Kang, Yusu Circuits Analysis &amp; Design, 4 ISBN-10: 0073380628.</li> <li>Ronald Mehler, Digital Integ Verilog, 1st edition, Newnes,</li> </ol>	z Sons, Inc., 2012, I Stephen H. Lewis, Circuits, 5th edition of Leblebici, Chilwood th edition, Mcgrav	SBN: 978 Robert Con, John o Kim, Cov-Hill High	8-0-470-' A. Meyer, Wiley & MOS Dig gher Edu	77010-8., Analysi Sons, Ingital Interaction, 2	s And c., 2009. egrated 2014.	

Course Name	Verification Practice	Course Code	EC501	18			
Offered By Department	Electronics and Communication Engineering	Structure(LTP C)	0	0	3	1.5	
To be offered for	M. Tech	Course Type	Core				
Prerequisite	Hold on Digital Logic Design, and HDL with design flow of VLSI Systems	Approved In	Senate		157	o	
Learning Objectives	To impart in depth knowledge and he Flow of Digital Circuits & Systems digital and analog building blocks.	. Analyses of comp	lex VLSI				
Learning Outcomes	Students would be able to design and analyse complex VLSI systems using industry level Design and verification tools.					ry level	
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	<ul> <li>Overview of the HDL and Delibertian of Understand and use the System Cluding new data types, literal relaxation of Verilog languatasks and functions, new hold clocking blocks, assertions, of Generate &amp; analyse function coverage</li> <li>Basic UVM constructs &amp; cla</li> <li>System Verilog/HDL verification stimulus, coverage, strings, these features for more effectory of the Power and Clock Routing, Information planning, placement of signoffs.</li> </ul>	tem Verilog/HDL R' terals, procedural b ge rules, fixes for sy ierarchy and conne over. Verify the des onal coverage, code asses, design a basic ation features, inclu queues and dynami tive and efficient ve atterconnects design	I'L design locks, sta ynthesis is ectivity for sign to en coverage test enviding clas c arrays, erification consider:	tements issues, eleatures, sure 100 e, line corronment ses, cons and learn. ations	, and openhancem and into % covera overage of using U trained in n how to	erators, lents to erfaces, age. & FSM VM random outilize	
Essential Reading	<ol> <li>Ming-Bo Lin, Introduction Perspective, CRC Press, 201</li> <li>SystemVerilog for Design: A of and Modeling, 2nd Edition, IS</li> </ol>	2, ISBN: 978-1-4398 Guide to Using Syst SBN-13: 978-03873	8-6859. em Verilo 33991	og for Ha	rdware D	)esign	
Supplementary Reading	<ol> <li>Chris Spear, SystemVerilog f Language Features, Springe</li> <li>Donald Thomas, Logic Design 1523364025.</li> <li>UVM Primer: A Step-by-S Methodology, 2013, ISBN: 09</li> </ol>	r. 2012, ISBBN: 978 and Verification Us tep Introduction	8-146140' sing Syste	7140. emVerilo	g, 2016, i	ISBN:	